

Low-Voltage, 0.45-Ω, SPDT Analog Switch

DESCRIPTION

The DG2717 is a low voltage, low on resistance, single-pole/double-throw (SPDT) monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low-power, high speed, low on-resistance, and small package size, the DG2717 is ideal for portable and battery power applications.

The DG2717 has an operation range from 1.6 V to 4.3 V single supply, and is low voltage logic compatible within this range, allowing the easy interface with low voltage DSP or MCU control logic. These traits make it ideal for one cell Li-ion battery direct power.

The switch conducts signals within power rails equally well in both directions when on, and blocks up to the power supply level when off. Break-before-make is guaranteed.

The DG2717 is built on Vishay Siliconix's sub micron CMOS low voltage process.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. For analog switching products manufactured in SC89 package, the lead (Pb)-free "E3" suffix is being used as a designator. It has a Tin device termination that meets all JEDEC standards for reflow and MSL rating.

FEATURES

- Low Voltage Operation (1.6 V to 4.3 V)
- Low On-Resistance r_{DS(on)}: 0.45 Ω Typ.
- Fast Switching t_{ON}: 22 ns, t_{OFF}: 8 ns
- · Low Leakage
- TTL/CMOS Compatible
- SC-89 (1.6 mm x 1.6 mm) Package

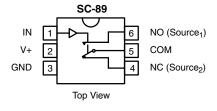
BENEFITS

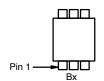
- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- · Reduce Board Space

APPLICATIONS

- · Cellular Phones
- PMP/MP3
- · Audio and Video Signal Routing
- Power Switch
- · Reed Relay Replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device Marking: Bx x = Date/Lot Traceability Code

TRUTH TABLE				
Logic	NC	NO		
0	ON	OFF		
1	OFF	ON		

ORDERING INFORMATION				
Temp Range	Package Part Number			
- 40 to 85 °C	SC89-6	DG2717DX-T1-E3		

DG2717

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ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND		- 0.3 to + 5.0	V		
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	v		
Continuous Current (NO, NC and COM Pins)		± 200	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 300	- IIIA		
Storage Temperature (D Suffix)		- 65 to 150	°C		
Power Dissipation (Packages) ^b	6-Pin SC89	172	mW		

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 2.15 mW/°C above 70 °C.

SPECIFICATIONS (V	/+ = 1.8 V						
		Test Condition Otherwise Unless Specified		Limits - 40 to 85 °C		С	
Parameter	Symbol	$V+ = 1.8 \text{ V}, \pm 10 \%, V_{IN} = 0.4 \text{ or } 1.0 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 0.2 V, I _{NO/NC} = 100 mA	Room Full		1.0	2.0 2.1	Ω
Digital Control							
Input High Voltage	V _{INH}		Full	1.0			V
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance ^d	C _{in}		Full		7		pF
Input Current ^f	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{NO} or V_{NC} = 1.5 V, R_L = 50 Ω , C_L = 35 pF R	Room Full ^d		54	74 81	
Turn-Off Time ^d	t _{OFF}		Room Full ^d		14	34 35	ns
Break-Before-Make Time ^d	t _d		Room	8			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		26		рC
Off-Isolation ^d	O _{IRR}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 54		i.
Crosstalk ^d	X _{TALK}		Room		- 60		dB
NO, NC Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		80		pF
Channel-On Capacitanced	C _{ON}	1	Room		180		1





Parameter		Test Condition Otherwise Unless Specified		Limits - 40 to 85 °C			
	Symbol	$V+ = 2.7 V \text{ to } 3.6 V, V_{IN} = 0.5 \text{ or } 1.4 V^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch							
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	V
On-Resistance	_	V+ = 2.7 V, V _{COM} = 1.5 V I _{NO} , I _{NC} = 100 mA	Room Full		0.5	0.7 0.8	
	r _{ON}	$V+ = 3.6 \text{ V}, V_{COM} = 0.5 \text{ V}, 2.0 \text{ V}$ $I_{NO}, I_{NC} = 100 \text{ mA}$	Room Full		0.45	0.65 0.75	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 0.6 \text{ V}, 2.1 \text{ V}$ $I_{NO}, I_{NC} = 100 \text{ mA}$	Room			0.2	
r _{ON} Match ^d	Δr _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 100 mA	Room			0.6	
Switch Off Leakage Current	I _{NO(off)} , I _{NC(off)}	V+ = 4.3 V	Room Full	- 10 - 100		10 100	
	I _{COM(off)} V _{NO} , V _{NC} = 0.3 V / 4 V, V _{COM} = 4 V / 0.3 V	Room Full	- 10 - 100		10 100	n/	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 4.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V} / 4 \text{ V}$	Room Full	- 10 - 100		10 100	
Digital Control	,						
Input High Voltage	V _{INH}		Full	1.4			V
Input Low Voltage	V _{INL}		Full			0.5	Ľ
Input Capacitance ^d	C _{in}		Full		7		pl
Input Current ^f	I _{INL} or I _{INH}	$V_{IN} = 0 V \text{ or } V+$	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V+ = 3.0 V, V _{NO} or V _{NC} = 1.5 V	Room Full		22	44 48	
Turn-Off Time	t _{OFF}	$R_L = 300 \Omega$, $C_L = 35 pF$ Figure 1 and 2	Room Full		8	29 30	ns
Break-Before-Make Time	t _d		Room	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		28		p(
Off-Isolation ^d	O _{IRR}	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 54		dl
Crosstalk ^d	X _{TALK}	11_ = 30 \$2, OL = 3 pr, r = 1 MIPZ	Room		- 57		
NO, NC Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		76		pl
Channel-On Capacitance ^d	C _{ON}]	Room		178		
Power Supply	•				•	•	
Power Supply Range	V+			1.6		4.3	٧
Power Supply Current	I+	$V+ = 3.6 \text{ V}, V_{IN} = 0 \text{ or } V+$			0.01	1.0	μA

Notes

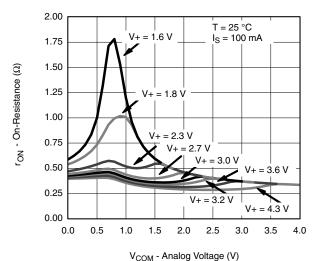
- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

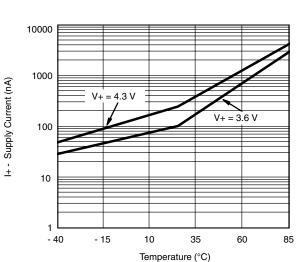
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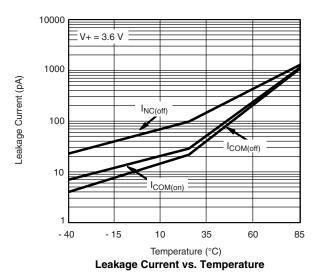
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

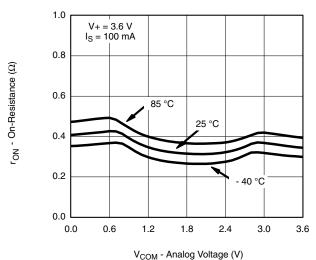


r_{ON} vs. V_{COM} and Single Supply Voltage

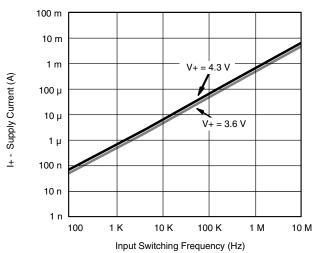


Supply Current vs. Temperature

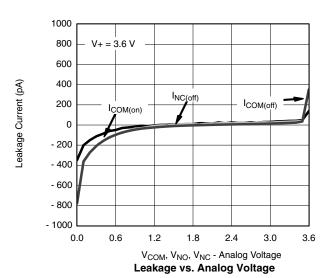




r_{ON} vs. Analog Voltage and Temperature

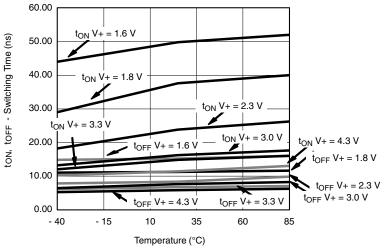


Supply Current vs. Input Switching Frequency

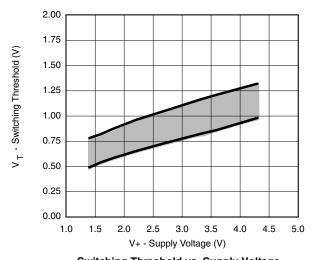




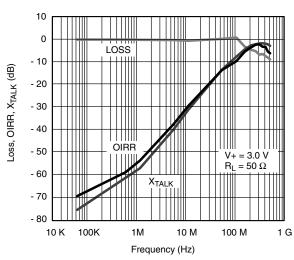
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



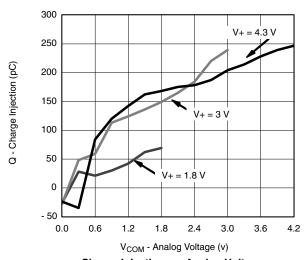
Switching Time vs. Temperature



Switching Threshold vs. Supply Voltage



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

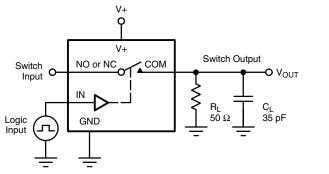


Charge Injection vs. Analog Voltage

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TEST CIRCUITS



 $\begin{array}{c} V_{INH} \\ V_{INL} \\ \\ 0 \ V \\ \\ t_{ON} \\ \end{array} \begin{array}{c} t_r < 5 \ ns \\ \\ t_f < 5 \ ns \\ \\ \\ t_{OFF} \\ \end{array}$

C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

Logic Input

Switch Output

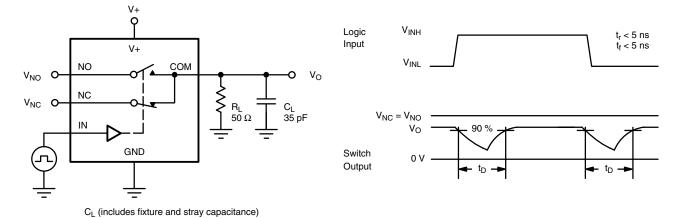


Figure 2. Break-Before-Make Interval

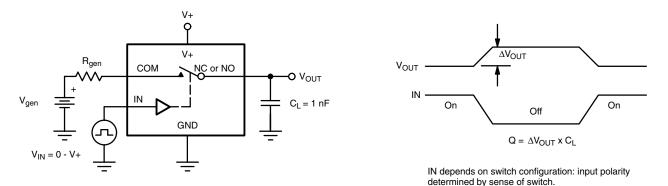


Figure 3. Charge Injection



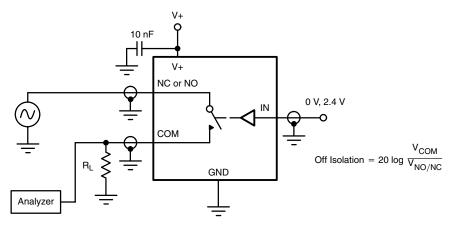


Figure 4. Off-Isolation

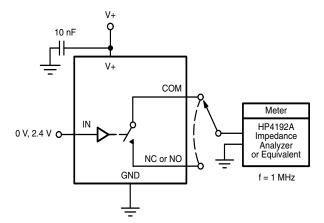


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73538.

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